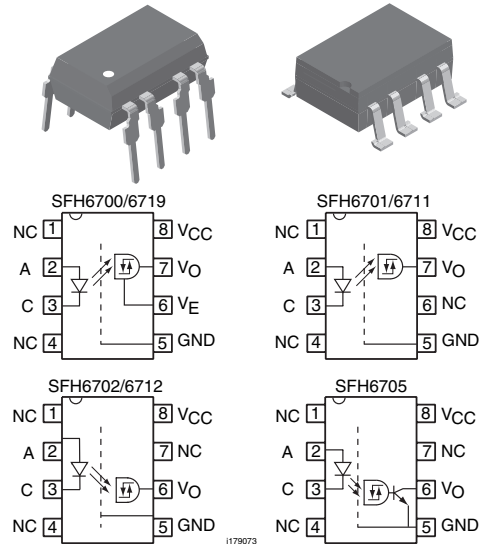


High Speed Optocoupler, 5 MBd, 1 kV/ μ s dV/dt

Features

- Data Rate 5.0 Mbits/s (2.5 Mbit/s over Temperature)
- Buffer
- Isolation Test Voltage, 5300 V RMS for 1.0 s
- TTL, LSTTL and CMOS Compatible
- Internal Shield for Very High Common Mode Transient Immunity
- Wide Supply Voltage Range (4.5 to 15 V)
- Low Input Current (1.6 mA to 5.0 mA)
- Three State Output (SFH6700/ 19)
- Totem Pole Output (SFH6701/ 02/ 11/ 12)
- Open Collector Output (SFH6705)
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Agency Approvals

- UL1577, File No. E52744 System Code H or J, Double Protection
- DIN EN 60747-5-2 (VDE0884)
DIN EN 60747-5-5 pending
Available with Option 1

Applications

Industrial Control
 Replace Pulse Transformers
 Routine Logic Interfacing
 Motion/Power Control
 High Speed Line Receiver
 Microprocessor System Interfaces
 Computer Peripheral Interfaces

Description

The SFH67xx high speed optocoupler series consists of a GaAlAs infrared emitting diode, optically coupled with an integrated photo detector. The detector incorporates a Schmitt-Trigger stage for improved noise immunity. Using the Enable input, the output can be switched to the high ohmic state, which is necessary for data bus applications. A Faraday shield provides a

common mode transient immunity of 1000 V/ μ at $V_{CM} = 50$ V for SFH6700/ 01/ 02/ 05 and 2500 V/ μ at $V_{CM} = 400$ V for SFH6711/ 12/ 19.

The SFH67xx uses an industry standard DIP-8 package. With standard lead bending, creepage distance and clearance of ≥ 7.0 mm with lead bending options 6, 7, and 9 ≥ 8 mm are achieved.



Order Information

Part	Remarks
SFH6700	Three State Output, DIP-8
SFH6701	Totem Pole Output, DIP-8
SFH6702	Totem Pole Output, DIP-8
SFH6705	Open Collector Output, DIP-8
SFH6711	Totem Pole Output, DIP-8
SFH6712	Totem Pole Output, DIP-8
SFH6719	Three State Output, DIP-8
SFH6700-X009	Three State Output, SMD-8 (option 9)
SFH6701-X006	Totem Pole Output, DIP-8 400 mil (option 6)
SFH6701-X007	Totem Pole Output, SMD-8 (option 7)
SFH6701-X009	Totem Pole Output, SMD-8 (option 9)
SFH6705-X006	Open Collector Output, DIP-8 400 mil (option 6)
SFH6705-X007	Open Collector Output, SMD-8 (option 7)
SFH6711-X007	Totem Pole Output, SMD-8 (option 7)

For additional information on the available options refer to Option Information.

Truth Table (Positive Logic)

	IR Diode	Enable	Output
SFH6700	on	H	Z
	off	H	Z
SFH6719	on	L	H
	off	L	L
SFH6701	on		H
	off		L
SFH6702	on		H
	off		L
SFH6705	on		H
	off		L
SFH6711	on		H
	off		L
SFH6712	on		H
	off		L

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

Input

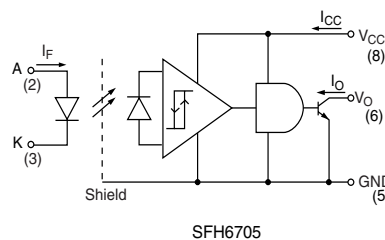
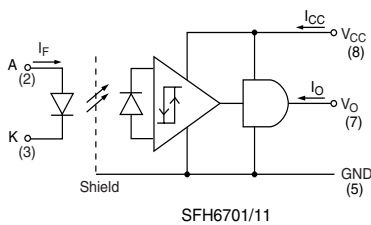
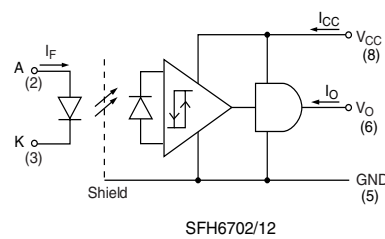
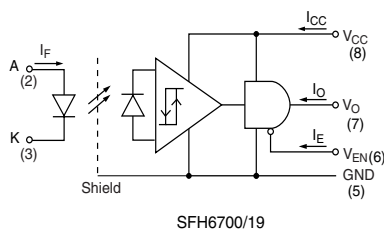
Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	3.0	V
DC Forward current		I_F	10	mA
Surge forward current	$t \leq 1.0\ \mu\text{s}$	I_{FSM}	1.0	A
Power dissipation		P_{diss}	20	mW

Output

Parameter	Test condition	Symbol	Value	Unit
Supply voltage		V_{CC}	- 0.5 to + 15	V
Three state enable voltage (SFH6700/19 only)		V_{EN}	- 0.5 to + 15	V
Output voltage		V_O	- 0.5 to + 15	V
Average output current		I_O	25	mA
Power dissipation		P_{diss}	100	mW

Coupler

Parameter	Test condition	Symbol	Value	Unit
Storage temperature range		T_{stg}	- 55 to + 125	°C
Ambient temperature range		T_{amb}	+ 85	°C
Lead soldering temperature	t = 10 s	T_{sld}	260	°C
Isolation test voltage		V_{ISO}	5300	V_{RMS}
Pollution degree			2.0	
Creepage distance and clearance	Standard lead bending		7.0	mm
	Options 6, 7, 9		8.0	mm
Comparative tracking index per DIN IEC 112/VDE 0303, part 1			175	
Isolation resistance	$V_{IO} = 500\text{ V}, T_{amb} = 25\text{ °C}$	R_{IO}	10^{12}	Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ °C}$	R_{IO}	10^{11}	Ω



isfh6700_01

Figure 1. Schematics

Recommended Operating Conditions

A 0.1 μ F bypass capacitor connected between pins 5 and 8 must be used.

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Supply voltage			V_{CC}	4.5		15	V
Enable voltage high		SFH6700	V_{EH}	2.0		15	V
		SFH6719	V_{EH}	2.0		15	V
Enable voltage low		SFH6700	V_{EL}	0		0.8	V
		SFH6719	V_{EL}	0		0.8	V
Forward input current			I_{Fon}	1.6 ⁽¹⁾		5.0	mA
			I_{Foff}			0.1	mA
Operating temperature			T_A	- 40		85	$^{\circ}$ C
Output pull-up resistor		SFH6705	R_L	350		4	k Ω
Fan Output	$R_L = 1.0$ k Ω	SFH6705	N			16	LS TTL Loads

⁽¹⁾ We recommended using a 2.2 mA to permit at least 20 % CTR degradation guard band.

Electrical Characteristics

- 40 $^{\circ}$ C $\leq T_{amb} \leq 85$ $^{\circ}$ C; 4.5 V $\leq V_{CC} \leq 15$ V; 1.6 mA $\leq I_{Fon} \leq 5.0$ mA; 2.0 $\leq V_{EH} \leq 15$ V; 0 $\leq V_{EL} \leq 0.8$ V; 0 mA $\leq I_{Foff} \leq 0.1$ mA;

Typical values: $T_{amb} = 25$ $^{\circ}$ C; $V_{CC} = 5.0$ V; $I_{Fon} = 3.0$ mA unless otherwise specified

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

Input

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 5.0$ mA	V_F		1.6	1.75	V
	$I_F = 5.0$ mA,	V_F			1.8	V
Input current hysteresis	$V_{CC} = 5.0$ V, $I_{HYS} = I_{Fon} - I_{Fon}$	I_{HYS}		0.1		mA
Reverse current	$V_R = 3.0$ V	I_R		0.5	10	μ A
Capacitance	$V_R = 0$ V, $f = 1.0$ MHz;	C_O		60		pF
Thermal resistance		R_{thja}		700		K/W

Output

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Logic low output voltage	$I_{OL} = 6.4 \text{ mA}$	V_{OL}			0.5	V
Logic high output voltage (except SFH6705)	$I_{OH} = 2.6 \text{ mA}, V_{OH} = V_{CC} - 1.8 \text{ V}$		2.4			V
Output leakage current ($V_{OUT} > V_{CC}$) (except SFH6705)	$V_O = 5.5 \text{ V}, V_{CC} = 4.5 \text{ V}, I_F = 5.0 \text{ mA}$	I_{OHH}		0.5	100	μA
	$V_O = 15 \text{ V}, V_{CC} = 4.5 \text{ V}, I_F = 5.0 \text{ mA}$	I_{OHH}		1.0	500	μA
Output leakage current (SFH705 only)	$V_O = 5.5 \text{ V}, V_{CC} = 5.5 \text{ V}, I_F = 5.0 \text{ mA}$	I_{OHH}		0.5	100	μA
	$V_O = 15 \text{ V}, V_{CC} = 15 \text{ V}, I_F = 5.0 \text{ mA}$	I_{OHH}		1.0	500	μA
Logic high enable voltage (SFH6700/19 only)		V_{EH}	2.0			V
Logic low enable voltage (SFH6700/19 only)		V_{EL}			0.8	V
Logic high enable current (SFH6700/19 only)	$V_{EN} = 2.7 \text{ V}$	I_{EH}			20	μA
	$V_{EN} = 5.5 \text{ V}$	I_{EH}			100	μA
	$V_{EN} = 15 \text{ V}$	I_{EH}		0.001	250	μA
Logic low enable current (SFH6700/19 only)	$V_{EN} = 0.4 \text{ V}$	I_{EL}	- 320	- 50		μA
High impedance state output current (SFH6700/19 only)	$V_O = 0.4 \text{ V}, V_{EN} = 2.0 \text{ V}, I_F = 5.0 \text{ mA}$	I_{OZL}	- 20			μA
	$V_O = 2.4 \text{ V}, V_{EN} = 2.0 \text{ V}, I_F = 0 \text{ mA}$	I_{OZH}			20	μA
	$V_O = 5.5 \text{ V}, V_{EN} = 2.0 \text{ V}, I_F = 0 \text{ mA}$	I_{OZH}			100	μA
		I_{OZH}		0.001	500	μA
Logic low supply current	$V_{CC} = 5.5 \text{ V}, I_F = 0$	I_{CCL}		3.7	6.0	mA
	$V_{CC} = 15 \text{ V}, I_F = 0$	I_{CCL}		4.1	6.5	mA
Logic high supply current	$V_{CC} = 5.5 \text{ V}, I_F = 5.0 \text{ mA}$	I_{CCH}		3.4	4.0	mA
	$V_{CC} = 15 \text{ V}, I_F = 5.0 \text{ mA}$	I_{CCH}		3.7	5.0	mA
Logic low short circuit output current ²⁾	$V_O = V_{CC} = 5.5 \text{ V}, I_F = 0$	I_{OSL}	25			mA
	$V_O = V_{CC} = 15 \text{ V}, I_F = 0$	I_{OSL}	40			mA
Logic high short circuit output current ²⁾	$V_{CC} = 5.5 \text{ V}, V_O = 0 \text{ V}, I_F = 5.0 \text{ mA}$	I_{OSL}			- 10	mA
	$V_{CC} = 15 \text{ V}, V_O = 0 \text{ V}, I_F = 5.0 \text{ mA}$	I_{OSL}			- 25	mA
Thermal resistance		R_{thja}		300		K/W

²⁾ Output short circuit time $\leq 10\text{ms}$.

Coupler

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Capacitance (input-output)	$f = 1.0 \text{ MHz}$, pins 1-4 and 5-8 shorted together	C_{IO}		0.6		pF
Isolation resistance	$V_{IO} = 500 \text{ V}, T_{amb} = 25 \text{ }^\circ\text{C}$	R_{IO}	10^{12}			Ω
	$V_{IO} = 500 \text{ V}, T_{amb} = 100 \text{ }^\circ\text{C}$	R_{IO}	10^{11}			Ω

Switching Characteristics

0 °C ≤ T_{amb} ≤ 85 °C; 4.5 V ≤ V_{CC} ≤ 15 V; 1.6 mA ≤ I_{Fon} ≤ 5.0 mA; 2.0 ≤ V_{EH} ≤ 15 V (SFH6700/19); 0 ≤ V_{EL} ≤ 0.8 V (SFH6700/19); 0 mA ≤ I_{Foff} ≤ 0.1 mA

Typical values: T_{amb} = 25 °C; V_{CC} = 5.0 V; I_{Fon} = 3.0 mA unless otherwise specified. ⁽³⁾

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Propagation delay time to logic low output level, SFH6700/01/02/11/12/19	Without peaking capacitor	t _{PHL}		120		ns
	With peaking capacitor	t _{PHL}		115	300	ns
		t _{PLH}		125		ns
		t _{PLH}		90	300	ns
Output enable time to logic high (SFH6700/19)		t _{PZH}		20		ns
Output enable time to logic low (SFH6700/19)		t _{PZL}		25		ns
Output disable time from logic low (SFH6700/19)		t _{PLZ}		50		ns
Output rise time	10 % to 90 %	t _r		40		ns
Output fall time	90 % to 10 %	t _f		10		ns

⁽³⁾ A 0.1 μF bypass capacitor connected between pins 5 and 8 must be used

Typical values: T_{amb} = 25 °C, V_{CC} = 5.0 V; I_{Fon} = 3.0 mA; R_L = 390 Ω unless otherwise specified ⁽³⁾

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Propagation delay time to logic low output level	Without peaking capacitor	SFH6705	t _{PHL}		115		ns
	With peaking capacitor	SFH6705	t _{PHL}		105	300	ns
	Without peaking capacitor	SFH6705	t _{PLH}		125		ns
	With peaking capacitor	SFH6705	t _{PLH}		90	300	ns
Output rise time	10 % to 90 %		t _r		25		ns
	90 % to 10 %		t _r		4		ns

Common Mode Transient Immunity

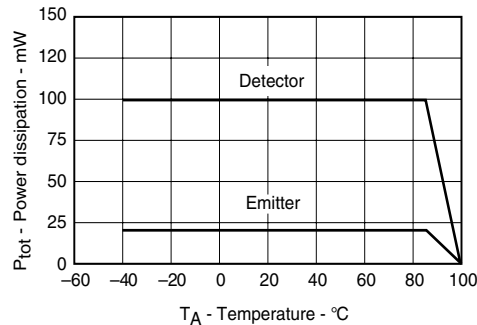
$T_{amb} = 25\text{ }^{\circ}\text{C}$, $V_{CC} = 5.0\text{ V}$ ⁽⁴⁾

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Logic High Common Mode Transient Immunity	$ V_{CM} = 50\text{ V}$, $I_F = 1.6\text{ mA}$	SFH6700	$ CM_H $ ⁽⁴⁾	1000			V/ μs
		SFH6701	$ CM_H $ ⁽⁴⁾	1000			V/ μs
		SFH6702	$ CM_H $ ⁽⁴⁾	1000			V/ μs
		SFH6705	$ CM_H $ ⁽⁴⁾	1000			V/ μs
	$ V_{CM} = 400\text{ V}$, $I_F = 1.6\text{ mA}$	SFH6711	$ CM_H $ ⁽⁴⁾	2500			V/ μs
		SFH6712	$ CM_H $ ⁽⁴⁾	2500			V/ μs
SFH6719		$ CM_H $ ⁽⁴⁾	2500			V/ μs	
Logic Low Common Mode Transient Immunity	$ V_{CM} = 50\text{ V}$, $I_F = 0\text{ mA}$	SFH6700	$ CM_L $ ⁽⁴⁾	1000			V/ μs
		SFH6701	$ CM_L $ ⁽⁴⁾	1000			V/ μs
		SFH6702	$ CM_L $ ⁽⁴⁾	1000			V/ μs
	$ V_{CM} = 400\text{ V}$, $I_F = 0\text{ mA}$	SFH6705	$ CM_L $ ⁽⁴⁾	1000			V/ μs
		SFH6711	$ CM_L $ ⁽⁴⁾	2500			V/ μs
		SFH6712	$ CM_L $ ⁽⁴⁾	2500			V/ μs
SFH6719	$ CM_L $ ⁽⁴⁾	2500			V/ μs		

⁽⁴⁾ CM_H is the maximum slew rate of a common mode voltage V_{CM} at which the output voltage remains at logic high level ($V_O > 2.0\text{ V}$)

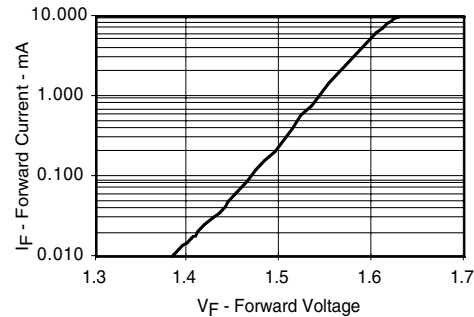
CM_L is the maximum slew rate of a common mode voltage V_{CM} at which the output voltage remains at logic low level ($V_O < 0.8\text{ V}$)

Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)



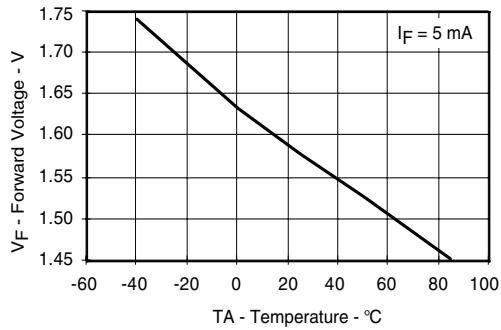
isf6700_02

Figure 2. Permissible Total Power Dissipation vs. Temperature



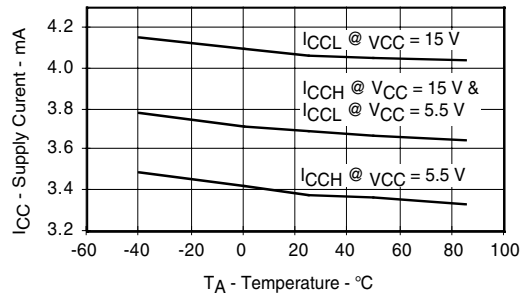
isf6700_03

Figure 3. Typical Input Diode Forward Current vs. Forward Voltage



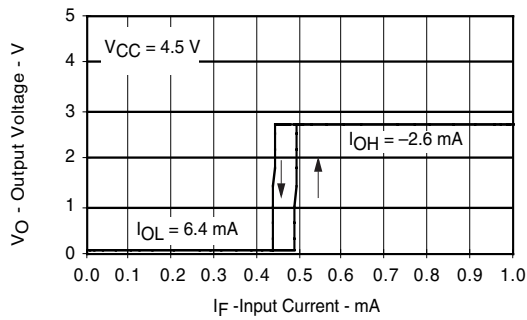
isfh6700_04

Figure 4. Typical Forward Input Voltage vs. Temperature



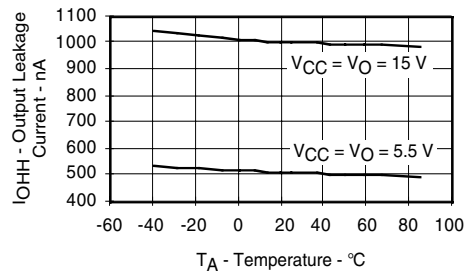
isfh6700_07

Figure 7. Typical Supply Current vs. Temperature



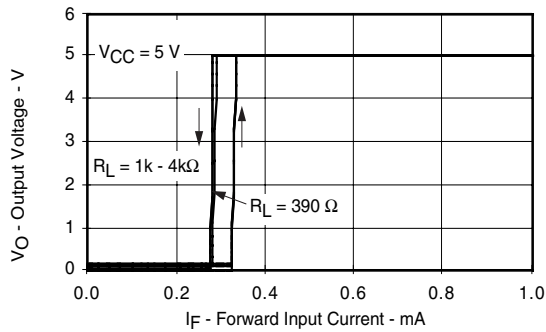
isfh6700_05

Figure 5. Typical Output Voltage vs. Forward Input Current (except SFH6705)



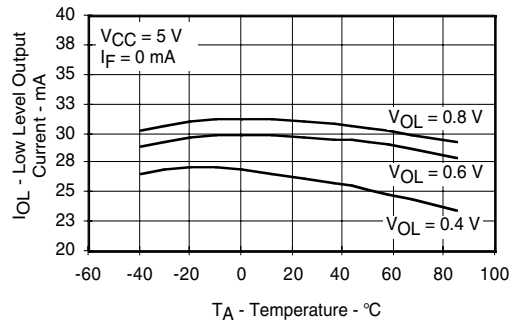
isfh6700_08

Figure 8. Typical Output Leakage Current vs. Temperature



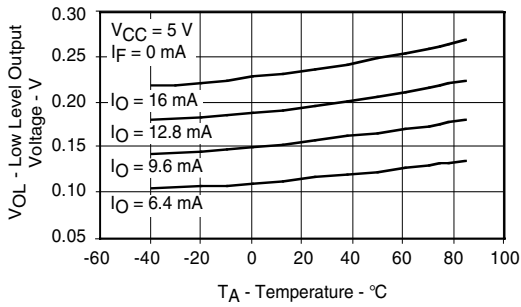
isfh6700_06

Figure 6. Typical Output Forward Voltage vs. Forward Input Current (only SFH6705)



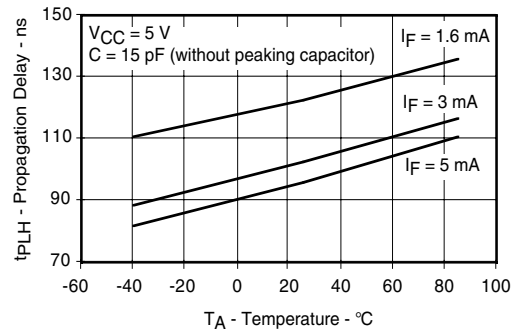
isfh6700_09

Figure 9. Typical Low Level Output Current vs. Temperature



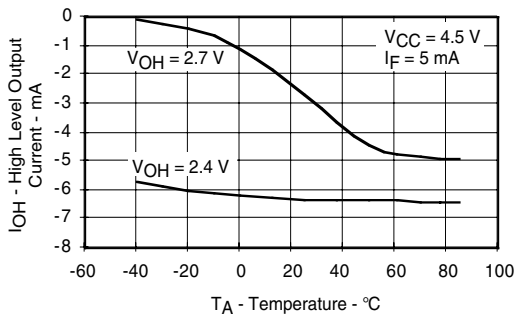
isfh6700_10

Figure 10. Typical Low Level Output Voltage vs. Temperature



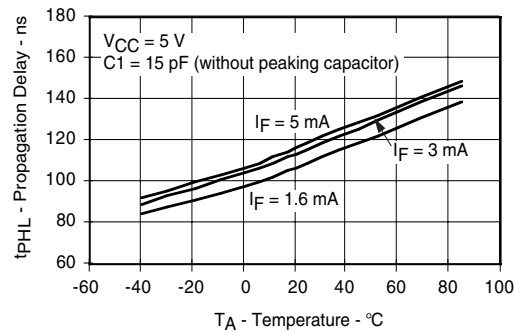
isfh6700_24

Figure 13. Typical Propagation Delay to Logic High vs. Temperature (except SFH6705)



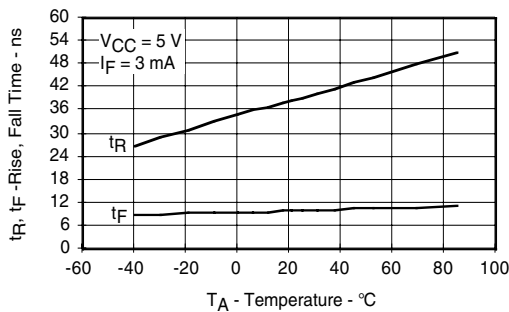
isfh6700_11

Figure 11. Typical High Level Output Current vs. Temperature (except SFH6705)



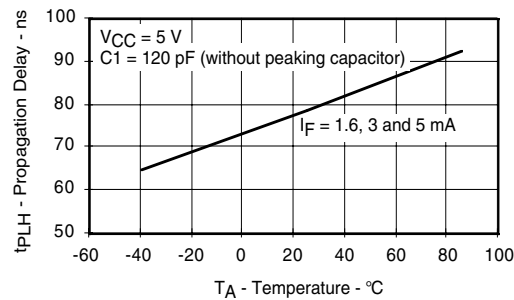
isfh6700_14

Figure 14. Typical Propagation Delay to Logic Low vs. Temperature (except SFH6705)



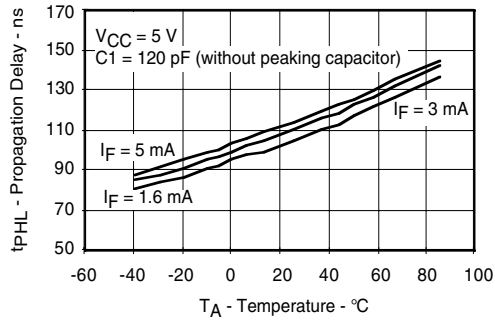
isfh6700_12

Figure 12. Typical Rise, Fall Time vs. Temperature (except SFH6705)



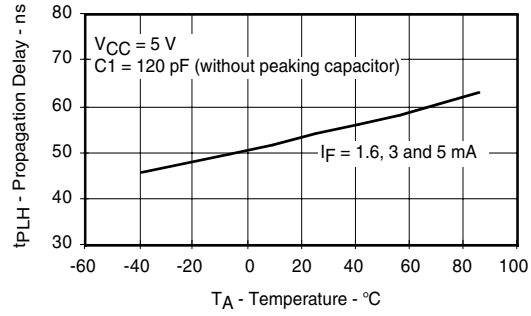
isfh6700_15

Figure 15. Typical Propagation Delays to Logic High vs. Temperature (except SFH6705)



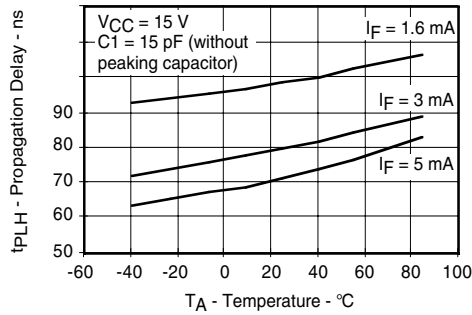
isfh6700_16

Figure 16. Typical Propagation Delay to Logic Low vs. Temperature



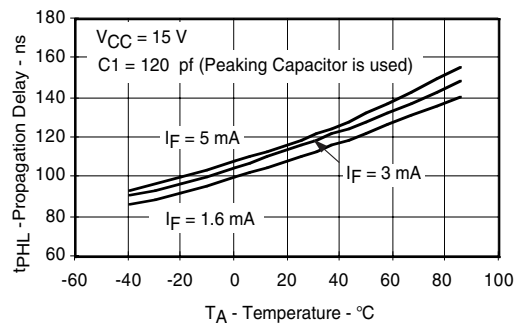
isfh6700_19

Figure 19. Typical Propagation Delays to Logic High vs. Temperature



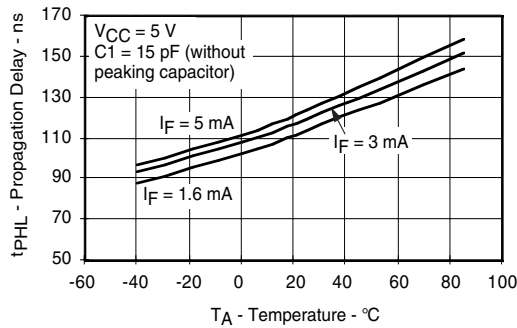
isfh6700_17

Figure 17. Typical Propagation Delays to Logic High vs. Temperature



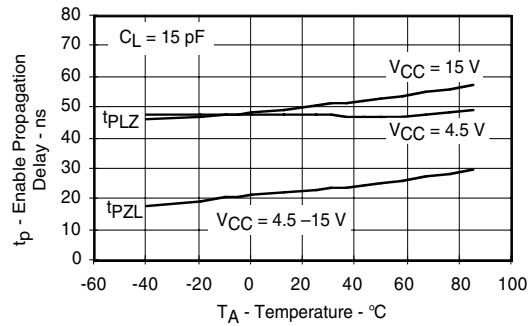
isfh6700_20

Figure 20. Typical propagation delays to Logic Low vs. temperature (except SFH6705)



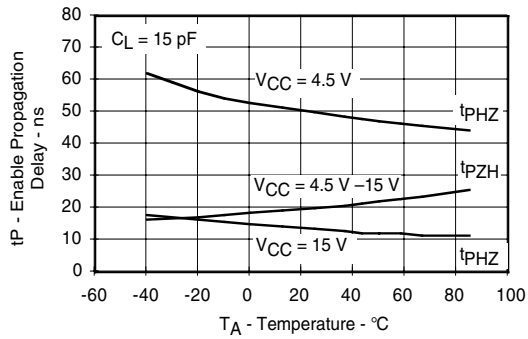
isfh6700_18

Figure 18. Typical Propagation Delays to Logic Low vs. Temperature



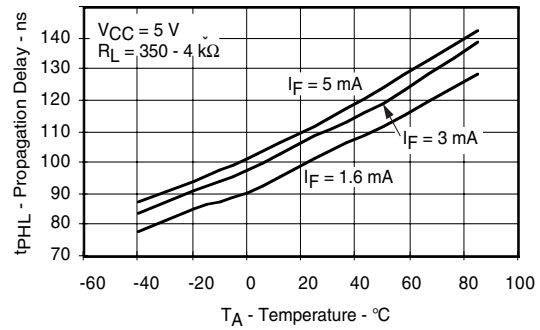
isfh6700_21

Figure 21. Typical Logic Low Enable Propagation Delays vs. Temperature (only SFH6700/11)



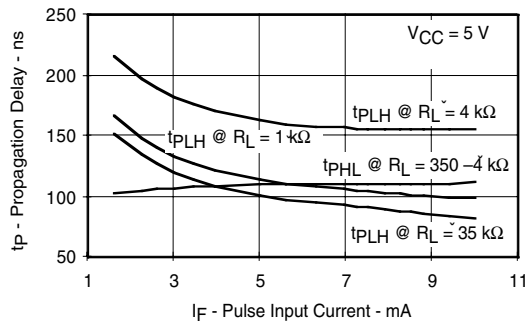
ish6700_22

Figure 22. Typical Logic High Enable Propagation Delays vs. Temperature (only SFH6700/11)



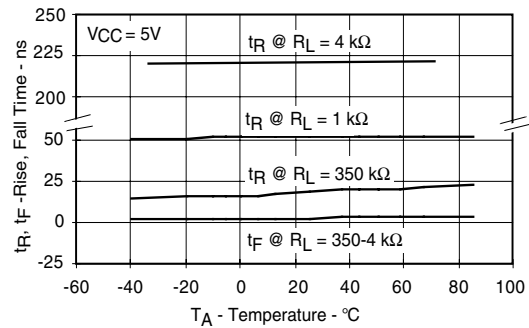
ish6700_25

Figure 25. Typical Propagation Delays to Low Level vs. Temperature (only SFH6705)



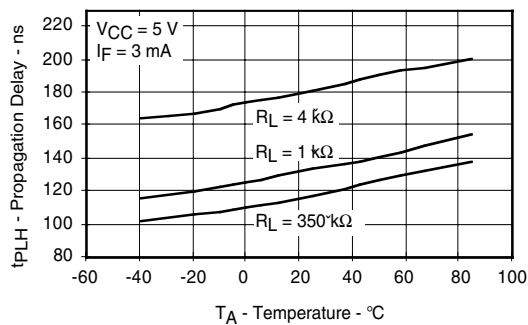
ish6700_23

Figure 23. Typical Propagation Delays vs. Pulse Input Current (only SFH6705)



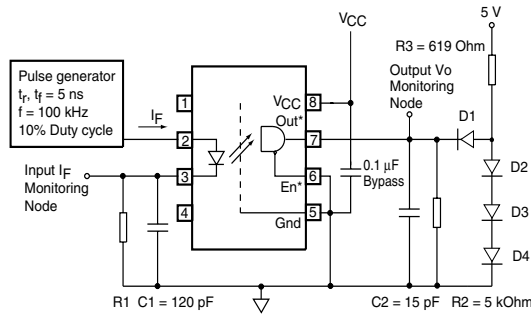
ish6700_26

Figure 26. Typical Rise, Fall Time vs. Temperature (only SFH6705)



ish6700_24

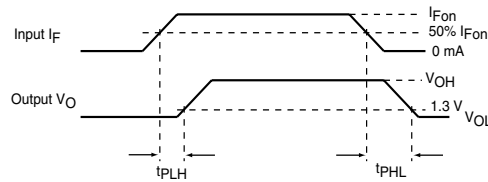
Figure 24. Typical Propagation Delays to High Level vs. Temperature (only SFH6705)



The Probe and Jig Capacitances are included in C1 and C2 All diodes are 1N916 or 1N3064

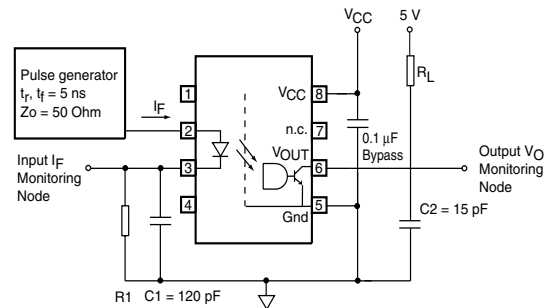
R1	2.15 kOhm	1.1 kOhm	681 Ohm
I _F (ON)	1.6 mA	3 mA	5 mA

* SFH6701/02/11/12 without V_{EN}
* SFH6702/12 Pin 6 V_{OJT} and Pin 7 n.c.



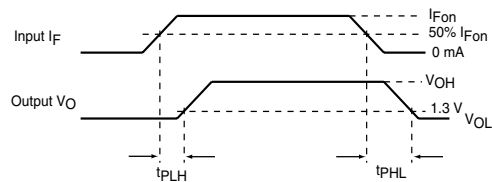
sfh6700_27

Figure 27. Test Circuit for t_{PLH}, t_{PHL}, t_r and t_f



The Probe and Jig Capacitances are included in C1 and C2

R1	2.15 kOhm	1.1 kOhm	681 Ohm
I _F (ON)	1.6 mA	3 mA	5 mA



sfh6700_28

Figure 28. Test Circuit for t_{PLH}, t_{PHL}, t_r and - SFH6705

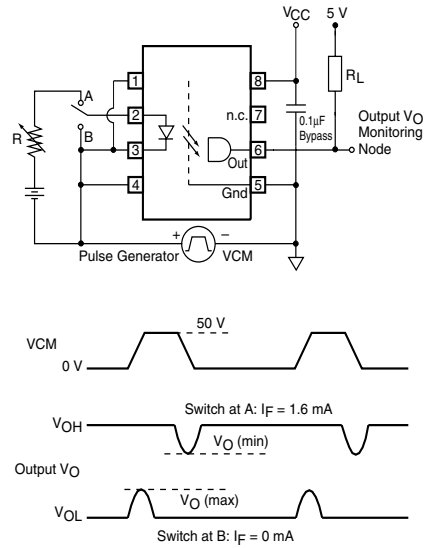
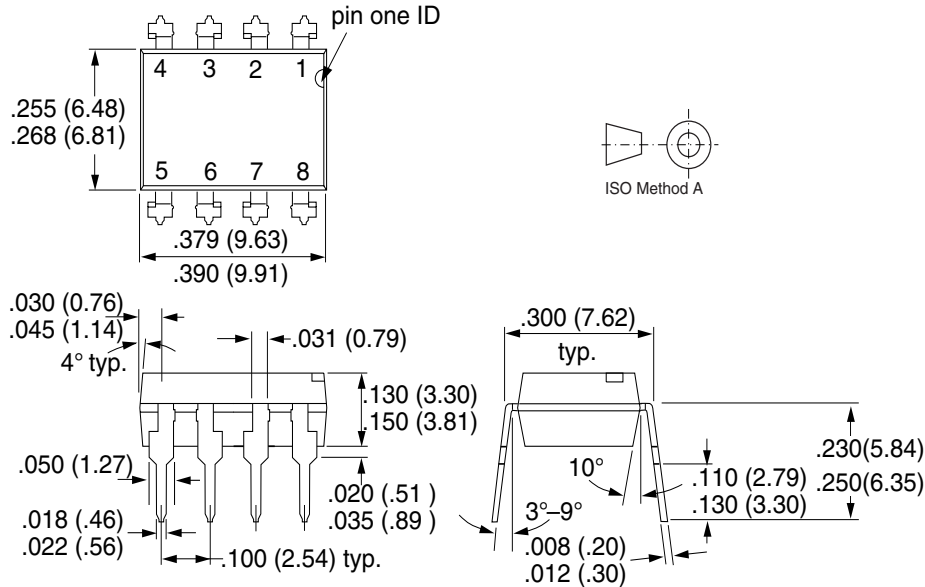
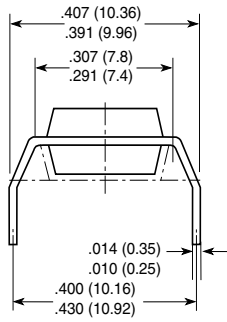


Figure 31. Test Circuit for Common Mode Transient Immunity and Typical Waveforms-SFH6705

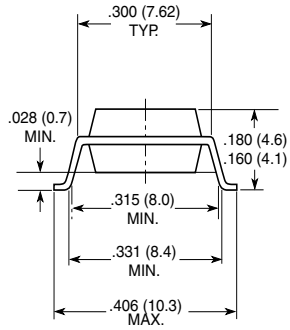
Package Dimensions in Inches (mm)



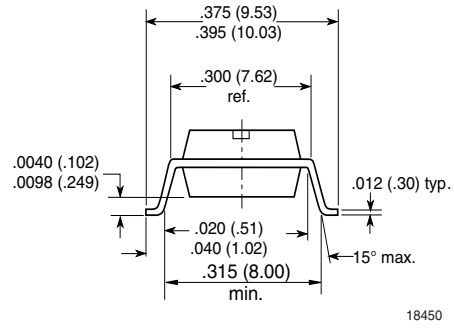
Option 6



Option 7



Option 9



18450



Vishay Semiconductors

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.